PATENT ABSTRACTS OF JAPAN

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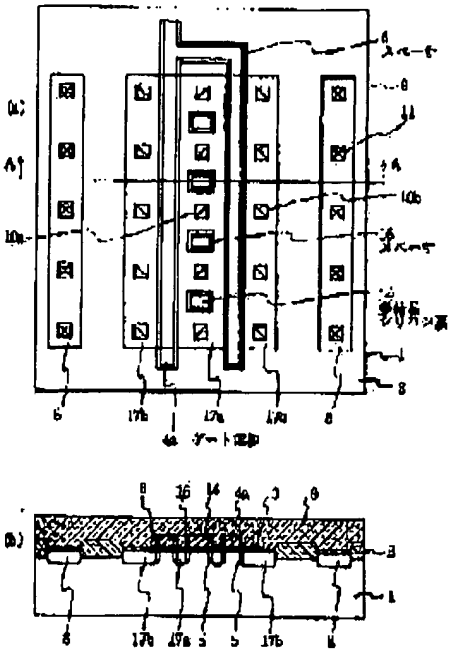
(54) MOS TRANSISTOR FOR INPUT/OUTPUT PROTECTIVE DEVICE

(57)Abstract:

PURPOSE: To suppress the generation of a PN junction breakdown by forming a diffused drain layer between gate electrodes divided into two and by forming insular conductor films of the same material as that of the gate electrodes in positions separated from the gate electrodes.

CONSTITUTION: A gate electrode 4a composed of polycrystalline silicon film is divided into two and a diffused drain layer 17a is formed between gate electrodes. Then, insular conductive films(polycrystalline silicon islands) 14 surrounded by the diffused drain layer 17a are formed of the same material as that of the gate electrodes in positions separated from the gate electrodes 4a. Thus, the length of the boundary between the gate electrodes 4a and diffused drain layer 17a composed of polycrystalline silicon film can be enlarged and a substrate current becomes higher even if the diffused drain layer is LDD structure so that it is possible to suppress the generation of a junction breakdown.



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